

Features

- 1000 Watts Peak Pulse Power per Line ($t_p = 8/20\mu s$)
- Bidirectional Configuration
- Protects One Power or I/O Port
- ESD Protection > 40 kilovolts
- Low Clamping Voltages

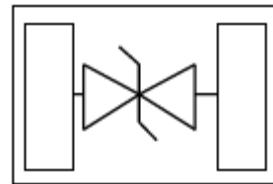


IEC Compatibility (EN61000-4)

- IEC 61000-4-2 (ESD) : $\pm 30kV$ (air), $\pm 30kV$ (contact)
- IEC 61000-4-4 (EFT) :40A (5/50ns)
- IEC 61000-4-5(Surge): 100A, 8/20 μs

Applications

- Ethernet - 10/100/1000 Base T
- Cellular Phones
- Handheld - Wireless Systems
- Personal Digital Assistant (PDA)
- USB Interface



Electrical Parameters

Parameter	Symbol	Value	Units
Peak pulse power ($t_p=8/20\mu s$)	P_{PP}	1000	Watts
Operating Temperature	T_J	-55°C ~ 125°C	°C
Storage Temperature	T_{STG}	-55°C ~ 150°C	°C

Electrical performance curve

V_{RWM} Reverse stand-off voltage

I_R Reverse leakage current

V_{CL} Clamping voltage

I_{PP} Peak pulse current

V_{TRIG} Reverse trigger voltage

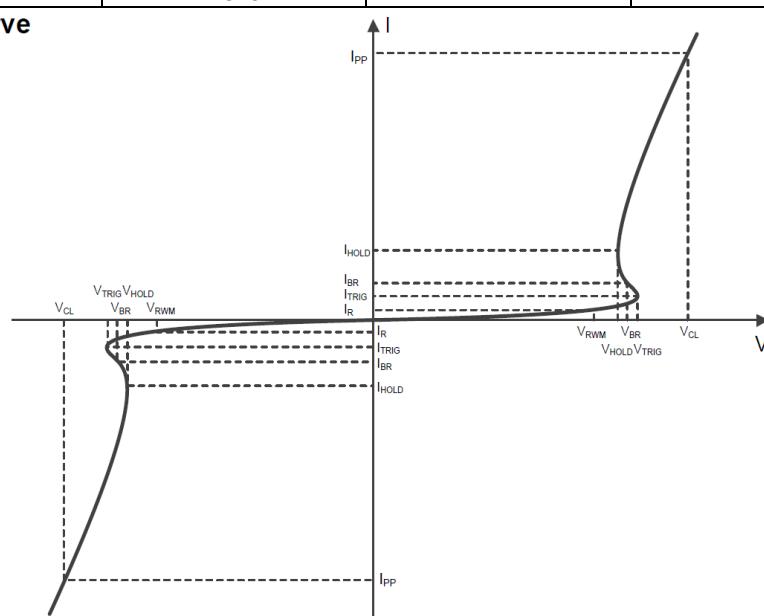
I_{TRIG} Reverse trigger current

V_{BR} Reverse breakdown voltage

I_{BR} Reverse breakdown current

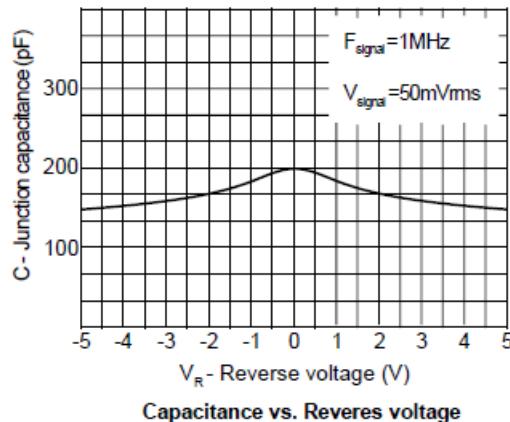
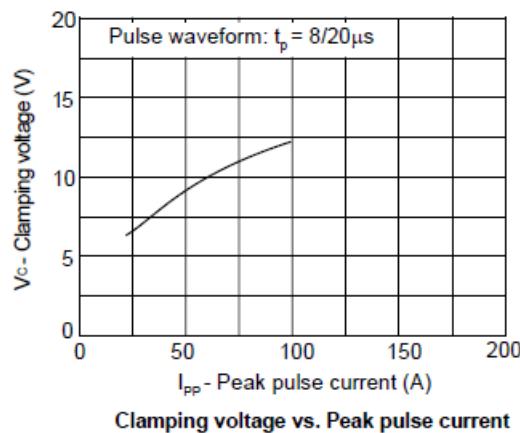
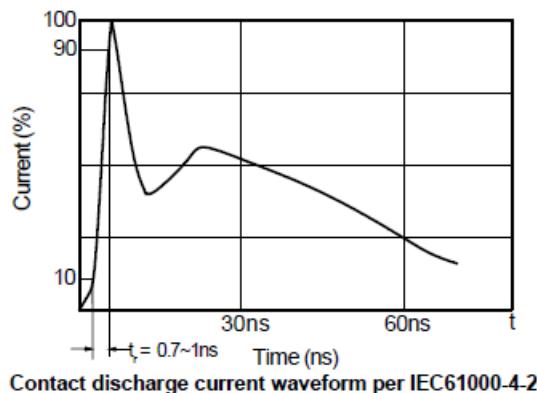
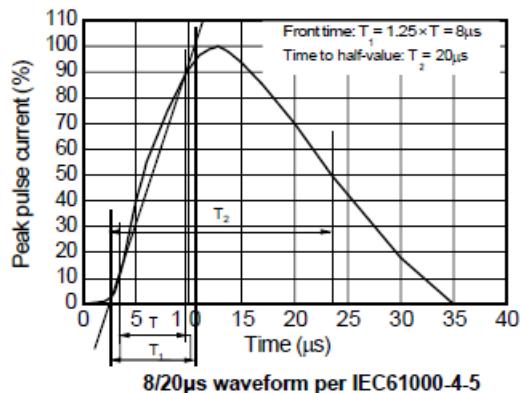
V_{HOLD} Reverse holding voltage

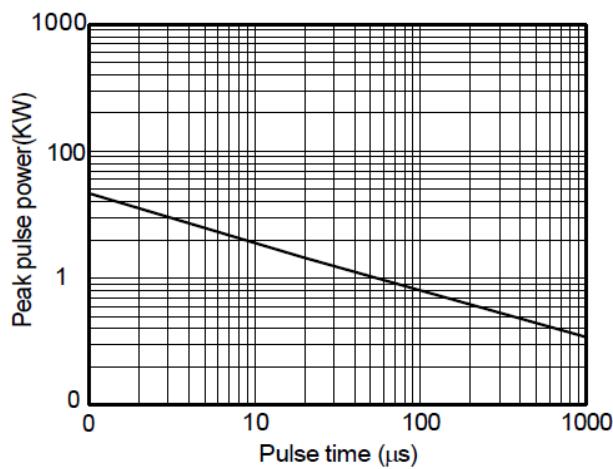
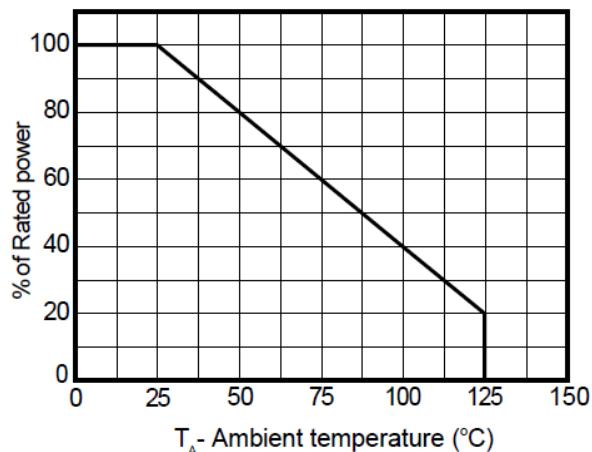
I_{HOLD} Reverse holding current



Ratings and characteristic curves ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Max	Units
Reverse Stand-off Voltage	V_{RWM}	Pin2 to 1/ Pin1 to 2		5.0	V
Reverse Breakdown Voltage	$V_{BR}(\text{min})$	$I_z=1\text{mA}$	5.5	7.5	V
Reverse Leakage Current	$I_R(\text{max})$	@ V_{RWM}		0.5	μA
Clamping Voltage	V_C	$I_{PP}=100\text{A}$ tp=8/20us		13.0	V
Peak Pulse Current	I_{PP}	tp=8/20us	100		A
Junction Capacitance	$C_{I/O}$	Pin capacitance to GND. Vdc=0V, f=1MHz	300		pf

Typical Characteristics



Non-repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature

Dimensions

DIMENSION OUTLINE:

Unit:mm

